

Abstract

The present invention provides a method for efficiently and completely removing a film deposited inside a film forming chamber. In addition, the invention provides a CVD apparatus using heating element which an in-situ cleaning method can be applied and its in-situ leaning method.

The removal method of this invention comprises a method for removing a film deposited inside a chamber which can be exhausted and/or on a member placed in the chamber, wherein after the chamber is exhausted, a heating element, at least the surface of which is composed of platinum, disposed in said vacuum chamber, is heated at a prescribed temperature and a cleaning gas which is decomposed and/or activated by the heating element to generate an activated species that converts the deposited film into gaseous substance is introduced into the chamber.